



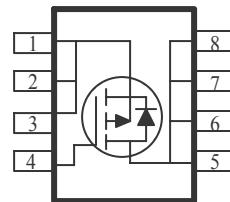
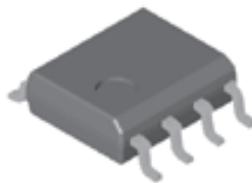
## P-Channel 40-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

### PRODUCT SUMMARY

$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
-40	35 @ $V_{GS} = -10V$	-9.0
	45 @ $V_{GS} = -4.5V$	-7.2



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$I_D$	-9.0	A
		-7.3	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	$\pm 50$	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	-2.1	A
Power Dissipation <sup>a</sup>	$P_D$	3.1	W
		2.6	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	50	°C/W
		92	°C/W

#### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

**SPECIFICATIONS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

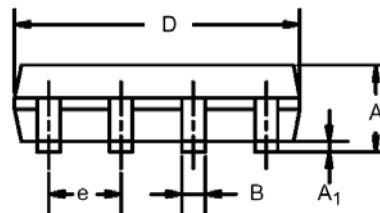
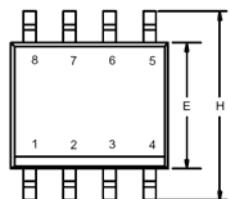
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Gate-Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1			
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			-5	
On-State Drain Current <sup>A</sup>	$I_{D(\text{on})}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			A
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}, I_D = -9.0 \text{ A}$			35	$\text{m}\Omega$
		$V_{GS} = -4.5 \text{ V}, I_D = -7.2 \text{ A}$			45	
Forward Transconductance <sup>A</sup>	$g_{fs}$	$V_{DS} = -15 \text{ V}, I_D = -9.0 \text{ A}$		31		S
Diode Forward Voltage	$V_{SD}$	$I_S = -2.1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.7		V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -9.0 \text{ A}$		15.3		nC
Gate-Source Charge	$Q_{gs}$			5.2		
Gate-Drain Charge	$Q_{gd}$			5.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega, I_D = -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6\Omega$		15		nS
Rise Time	$t_r$			12		
Turn-Off Delay Time	$t_{d(off)}$			62		
Fall-Time	$t_f$			46		

## Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

## Package Information

## SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	1.35	1.75	0.053	0.069
<b>A<sub>1</sub></b>	0.10	0.20	0.004	0.008
<b>B</b>	0.35	0.51	0.014	0.020
<b>C</b>	0.19	0.25	0.0075	0.010
<b>D</b>	4.80	5.00	0.189	0.196
<b>E</b>	3.80	4.00	0.150	0.157
<b>e</b>	1.27 BSC		0.050 BSC	
<b>H</b>	5.80	6.20	0.228	0.244
<b>h</b>	0.25	0.50	0.010	0.020
<b>L</b>	0.50	0.93	0.020	0.037
<b>q</b>	0°	8°	0°	8°

